

Title (en)

METHOD FOR MAKING A CIRCUITRY COMPRISING CONDUCTIVE TRACKS, CHIPS AND MICRO-VIAS AND USE OF SAME FOR PRODUCING PRINTED CIRCUITS AND MULTILAYER MODULES WITH HIGH DENSITY OF INTEGRATION

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER SCHALTUNGSANORDNUNG MIT LEITENDEN BAHNEN, ANSCHLUSSFLÄCHEN UND MIKROKONTAKTLÖCHERN UND ANWENDUNG DIESES VERFAHREN FÜR DIE HERSTELLUNG VON GEDRUCKTEN SCHALTUNGEN UND MEHRSCICHTIGEN MODULN MIT HOHER INTEGRATIONSDICHTHE

Title (fr)

PROCEDE DE REALISATION D'UNE CIRCUITERIE COMPORTANT PISTES, PASTILLES ET MICROTRAVERSEES CONDUCTRICES ET UTILISATION DE CE PROCEDE POUR LA REALISATION DE CIRCUITS IMPRIMES ET DE MODULES MULTICOUCHES A HAUTE DENSITE D'INTEGRATION

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Application

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Abstract (en)

[origin: WO211503A1] The invention concerns a method for making a circuitry comprising conductive tracks, chips and micro-vias, at the top surface of a dielectric (303) consisting of a polymer matrix, a compound capable of inducing subsequent metallization and, if required one or several non-conductive and inert fillers, said dielectric (303) covering a level of circuitry (302) or metallized layer, which comprises steps which consist in: a) perforating right through said dielectric (303) without perforating the subjacent metallized layer or the subjacent level of circuitry (302), so as to form one or several micro-vias (304) at desired sites; b) forming, by metallization, metal tracks (312), chips (313) and micro-vias (311) at the surface of the dielectric (314) and of the micro-vias (304), while providing selective protection by depositing a protective layer.

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